

Features

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R_{DS(ON)}
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 1

Maximum Ratings

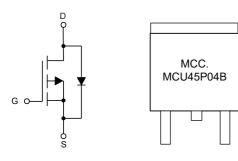
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient(Note 2)
- · Thermal Resistance: 2.2°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	-40	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		-45	Α	
	T _C =100°C	- I _D	-28		
Pulsed Drain Current ^(Note 3)		I _{DM}	-140	Α	
Total Power Dissipation ^(Note 4)		P _D	56	W	
Single Pulsed Avalanche Energy ^(Note 5)		E _{AS}	264	mJ	

Note:

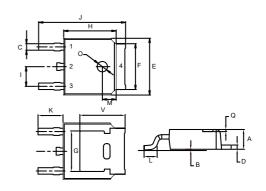
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. $T_J=25$ °C, $V_{DD}=-40V$, $V_{GS}=-10V$, L=0.5mH.

Internal Structure and Marking Code



P-CHANNEL MOSFET

DPAK(TO-252)



- Gate
- 2,4. Drain
 - 3. Source

DIMENSIONS					
DIM INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
- 1	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

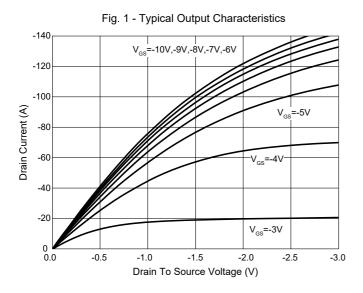


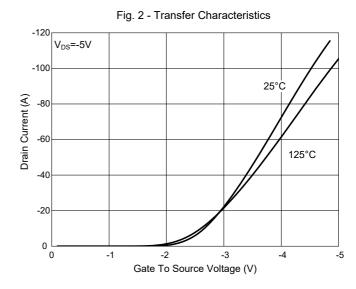
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

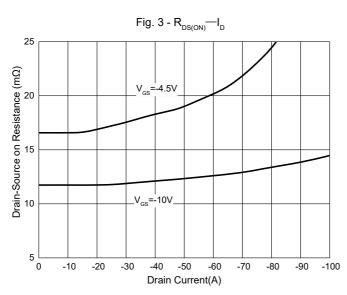
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-40			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V			-1	μA	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.3	V	
Drain-Source On-Resistance	Б	V _{GS} =-10V, I _D =-20A		11	14	0	
	R _{DS(on)}	V _{GS} =-4.5V, I _D =-10A		17 21		mΩ	
Gate Resistance	R _g	f=1MHz, Open drain		8.5		Ω	
Diode Characteristics							
Continuous Body Diode Current	Is				-45	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.2	V	
Reverse Recovery Time	t _{rr}	L 00A H / H 400A /		14.6		ns	
Reverse Recovery Charge	Q _{rr}	I _S =-20A, dI _F /dt=100A/μs		8.3		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			3433		pF	
Output Capacitance	C _{oss}	V_{DS} =-20V, V_{GS} =0V,f=1MHz		227			
Reverse Transfer Capacitance	C _{rss}			186			
Total Gate Charge	Qg			58			
Gate-Source Charge	Q _{gs}	V _{DS} =-20V,V _{GS} =-10V,I _D =-20A		13		nC	
Gate-Drain Charge	Q_{gd}			7.8			
Turn-On Delay Time	t _{d(on)}			7.9			
Turn-On Rise Time	t _r	V _{DS} =-20V, V _{GEN} =-10V,		61		no	
Turn-Off Delay Time	t _{d(off)}	$R_G=3.9\Omega$, $I_{DS}=-20A$		110		- ns	
Turn-Off Fall Time	t _f			70			

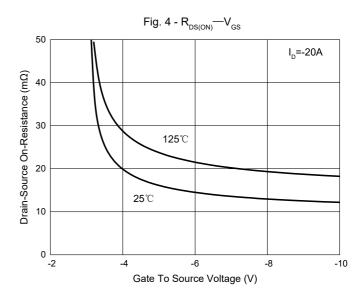


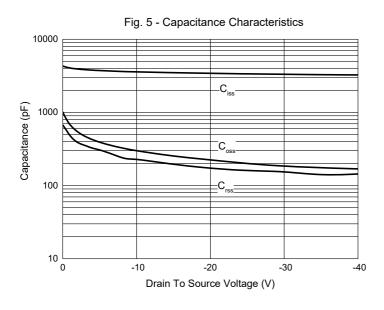
Curve Characteristics

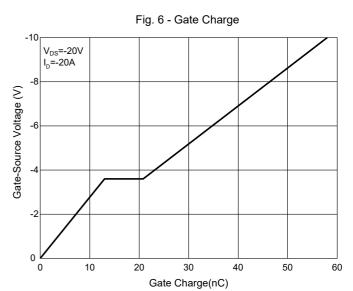






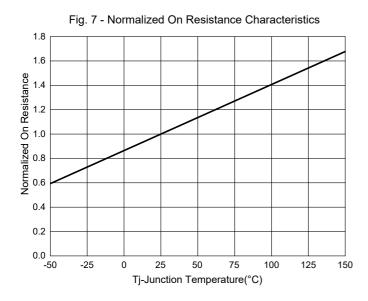


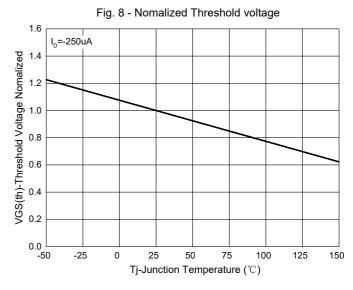


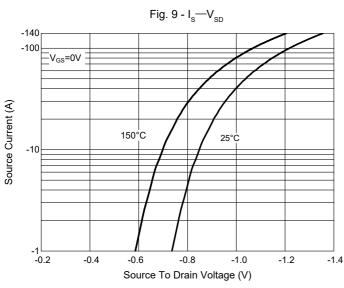


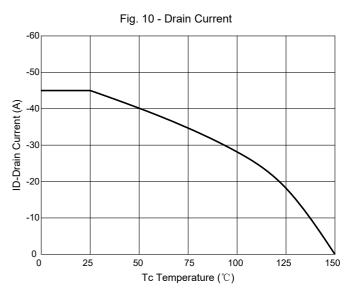


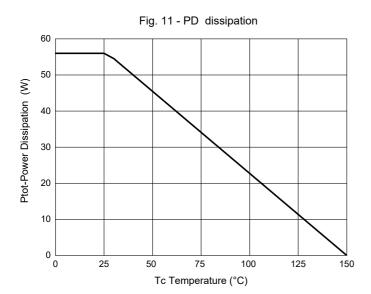
Curve Characteristics





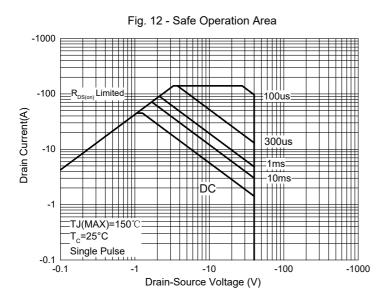








Curve Characteristics



10 D=T_o/T T_{J,PK}=T_c+P_{DM}·Z_{e,C}·R_{e,JC} R_{e,JC} R_{e,JC}

Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

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